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RLT80820G TECHNICAL DATA

High Power Infrared Laserdiode

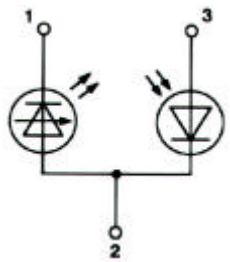
Structure: **GaAlAs double heterostructure**

Lasing wavelength: **808 nm typ.**

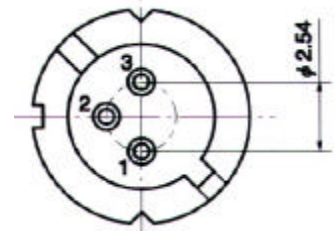
Max. optical power: **20 mW**

Package: **9 mm**

PIN CONNECTION:



- 1) Laser diode cathode
- 2) Laser diode anode and photodiode cathode
- 3) Photodiode anode



Absolute Maximum Ratings (T_c=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Optical Output Power	P _o	20	mW
LD Reverse Voltage	V _{R(LD)}	2	V
PD Reverse Voltage	V _{R(PD)}	30	V
Operating Temperature	T _C	-10 .. +40	°C
Storage Temperature	T _{STG}	-40 .. +85	°C

Optical-Electrical Characteristics (T_c = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Optical Output Power	P _o	cw			20	mW
Threshold Current	I _{th}	cw	20	25	45	mA
Operation Current	I _{op}	P _o = 20 mW		55	65	mA
Operation Voltage	V _{op}	P _o = 20 mW			2.7	V
Lasing Wavelength	λ _p	P _o = 20 mW	790	808	810	nm
Beam Divergence	θ _{//}	P _o = 20 mW	5	8	11	°
Beam Divergence	θ _⊥	P _o = 20 mW	25	31	37	°
Astigmatism	A _s	P _o = 20 mW, NA = 0.4		5		μm
Monitor Current	I _m	P _o = 20 mW, V _r = 5V		40	75	μA